CSD19506KCS 80V N-Channel NexFET™ Power MOSFET

1 Features

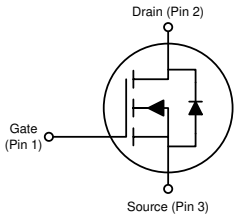
- Ultra-low Q_g and Q_{gd}
- Low thermal resistance
- Avalanche rated
- Pb-free terminal plating
- RoHS compliant
- Halogen free
- TO-220 plastic package

2 Applications

- Secondary side synchronous rectifier
- Motor control

3 Description

This 80V, 2.0mΩ, TO-220 NexFET™ power MOSFET is designed to minimize losses in power conversion applications.



Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	80		V
Q_g	Gate Charge Total (10V)	120		nC
Q_{gd}	Gate Charge Gate to Drain	20		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = 6V	2.2	mΩ
		V_{GS} = 10V	2.0	mΩ
$V_{GS(th)}$	Threshold Voltage	2.5		V

Ordering Information

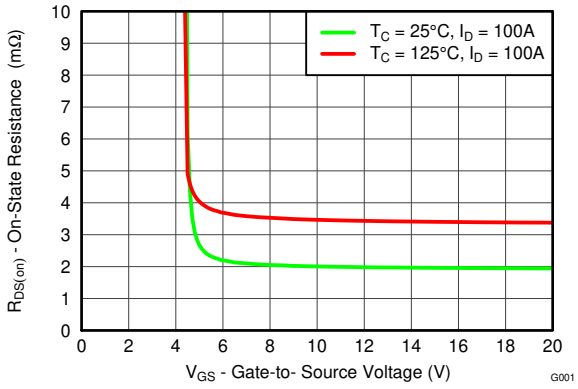
Device	Package[1]	Media	Qty	Ship
CSD19506KCS	TO-220 Plastic Package	Tube	50	Tube

(1) For all available packages, see the orderable addendum at the end of the data sheet.

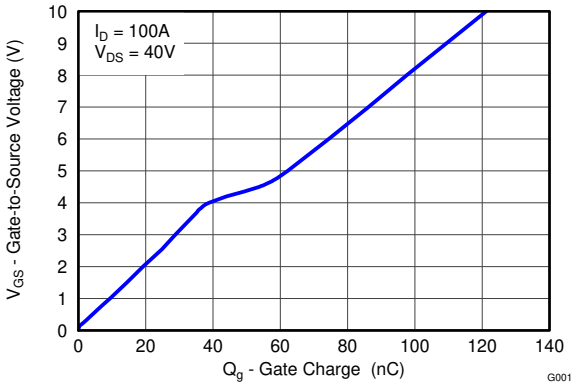
Absuloute Maximum Ratings

T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package limited)	150	A
	Continuous Drain Current (Silicon limited), T_C = 25°C	273	
	Continuous Drain Current (Silicon limited), T_C = 100°C	193	
I_{DM}	Pulsed Drain Current [1]	400	A
P_D	Power Dissipation	375	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 175	°C
E_{AS}	Avalanche Energy, single pulse I_D = 129A, L = 0.1mH, R_G = 25Ω	832	mJ

(1) Max $R_{\theta JC}$ = 0.4°C/W, pulse duration ≤100µs, duty cycle ≤1%



$R_{DS(on)}$ vs V_{GS}



Gate Charge

Table of Contents

4 Specifications

4.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0V, I_D = 250µA	80			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0V, V_{DS} = 64V			1	µA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0V, V_{GS} = 20V			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	2.1	2.5	3.2	V
$R_{DS(on)}$	Drain-to-Source On-Resistance	V_{GS} = 6V, I_D = 100A		2.2	2.8	mΩ
		V_{GS} = 10V, I_D = 100A		2.0	2.3	mΩ
g_{fs}	Transconductance	V_{DS} = 8V, I_D = 100A		297		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 40V, f = 1MHz		9380	12200	pF
C_{oss}	Output Capacitance			2260	2940	pF
C_{rss}	Reverse Transfer Capacitance			42	55	pF
R_G	Series Gate Resistance			1.3	2.6	Ω
Q_g	Gate Charge Total (10V)	V_{DS} = 40V, I_D = 100A		120	156	nC
Q_{gd}	Gate Charge Gate to Drain			20		nC
Q_{gs}	Gate Charge Gate to Source			37		nC
$Q_{g(th)}$	Gate Charge at V_{th}			25		nC
Q_{oss}	Output Charge	V_{DS} = 40V, V_{GS} = 0V		345		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 40V, V_{GS} = 10V, I_{DS} = 100A, R_G = 0Ω		19		ns
t_r	Rise Time			11		ns
$t_{d(off)}$	Turn Off Delay Time			30		ns
t_f	Fall Time			10		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{SD} = 100A, V_{GS} = 0V		0.9	1.1	V
Q_{rr}	Reverse Recovery Charge	V_{DS}= 40V, I_F = 100A, di/dt = 300A/µs		525		nC
t_{rr}	Reverse Recovery Time			107		ns

4.2 Thermal Information

(T_A = 25°C unless otherwise stated)[1]

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			0.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			62	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.

4.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

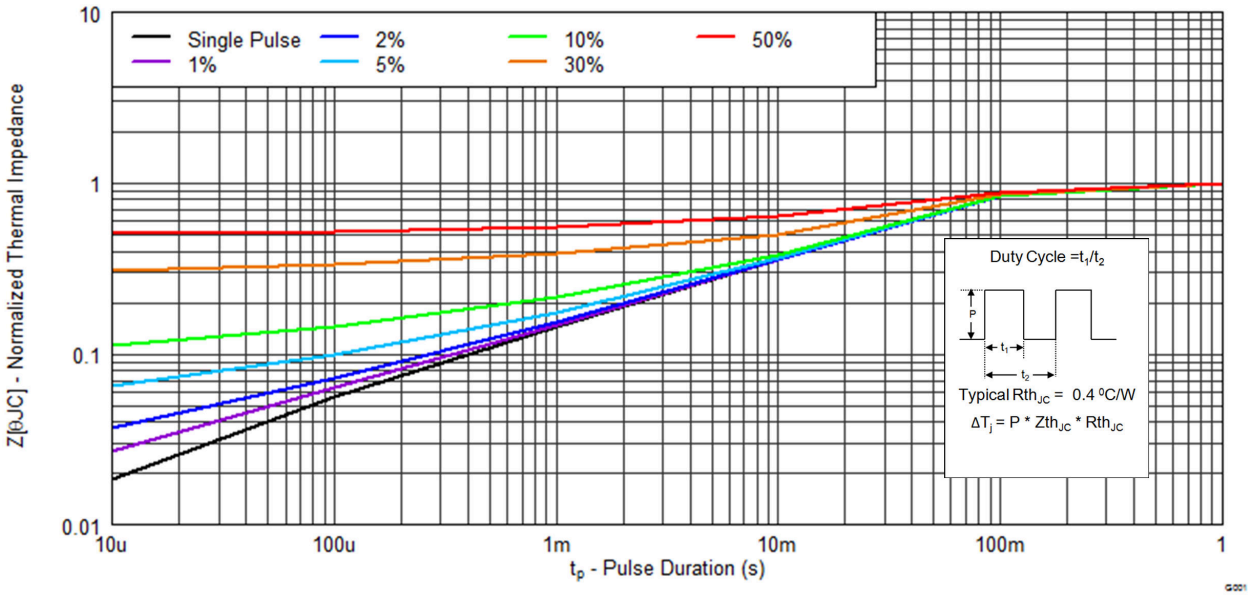


Figure 4-1. Transient Thermal Impedance

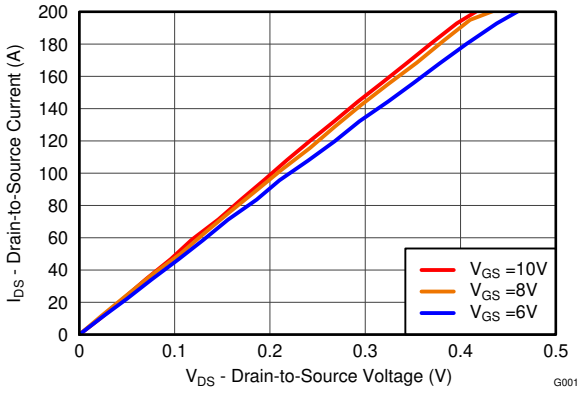


Figure 4-2. Saturation Characteristics

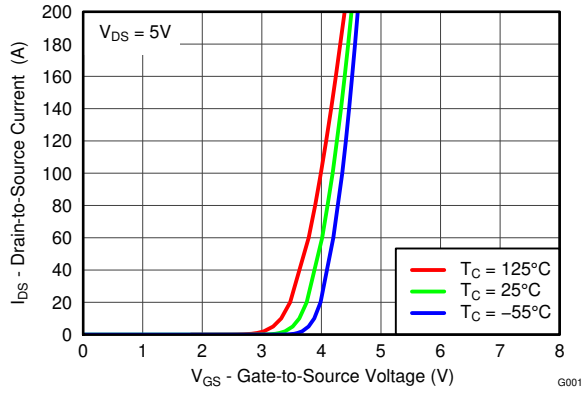


Figure 4-3. Transfer Characteristics

4.3 Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

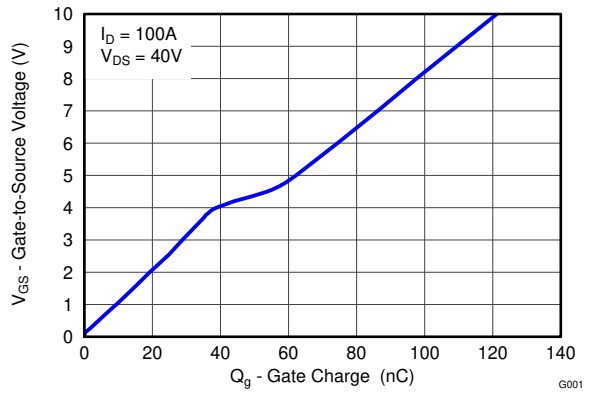


Figure 4-4. Gate Charge

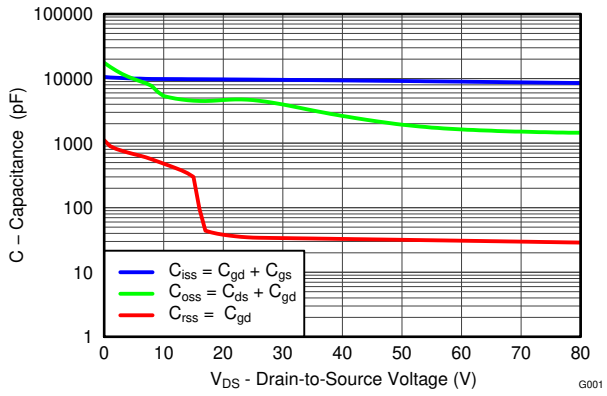


Figure 4-5. Capacitance

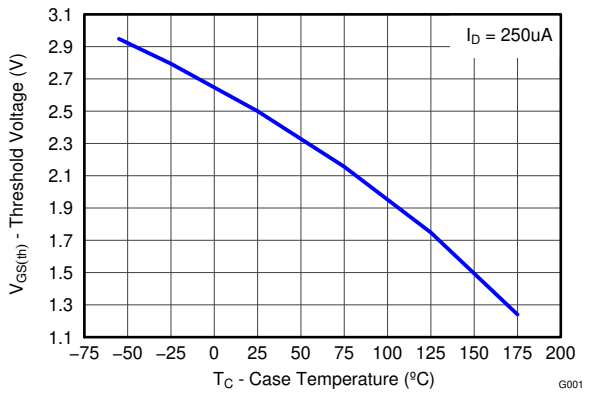


Figure 4-6. Threshold Voltage vs Temperature

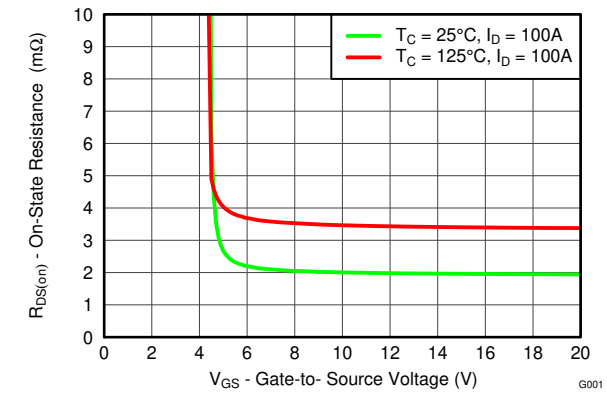


Figure 4-7. On-State Resistance vs Gate-To-Source Voltage

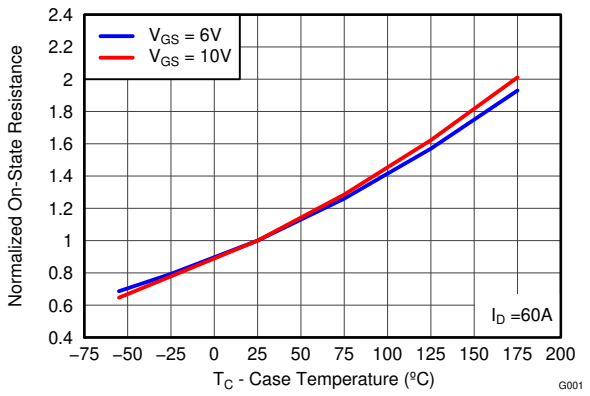


Figure 4-8. Normalized On-State Resistance vs Temperature

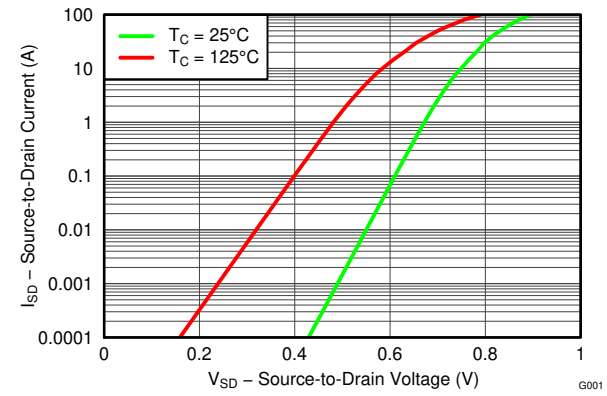


Figure 4-9. Typical Diode Forward Voltage

4.3 Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

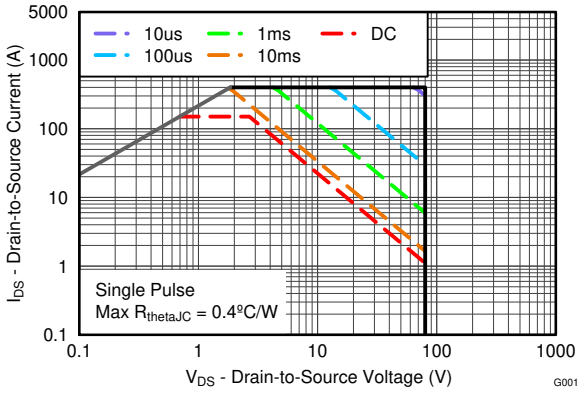


Figure 4-10. Maximum Safe Operating Area

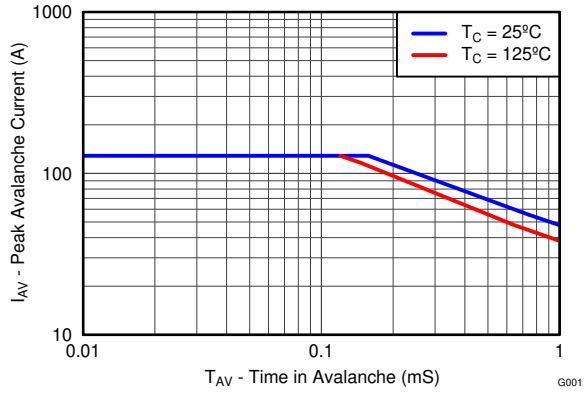


Figure 4-11. Single Pulse Unclamped Inductive Switching

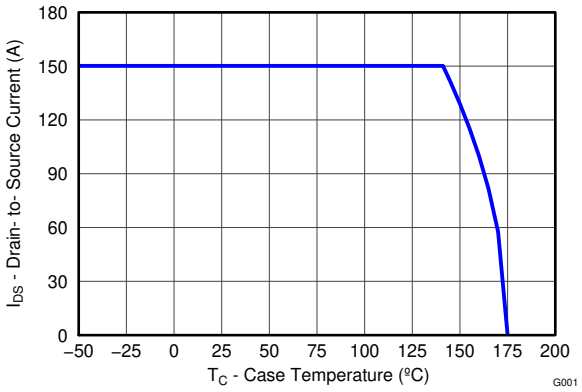


Figure 4-12. Maximum Drain Current vs Temperature

5 Device and Documentation Support

5.1 Third-Party Products Disclaimer

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5.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

5.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

6 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision B (October 2014) to Revision C (May 2024)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document	1

Changes from Revision A (February 2014) to Revision B (October 2014)	Page
• Changed Pulsed Drain Current Conditions	1
• Updated the SOA in Figure 4-10	4

Changes from Revision * (December 2013) to Revision A (February 2014)	Page
• Increased Package Current Limit to 150A	1
• Increased Pulsed Drain Current to 400A	1
• Updated SOA Curve	4

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD19506KCS	Active	Production	TO-220 (KCS) | 3	50 | TUBE	ROHS Exempt	SN	N/A for Pkg Type	-55 to 175	CSD19506KCS
CSD19506KCS.B	Active	Production	TO-220 (KCS) | 3	50 | TUBE	ROHS Exempt	SN	N/A for Pkg Type	-55 to 175	CSD19506KCS

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

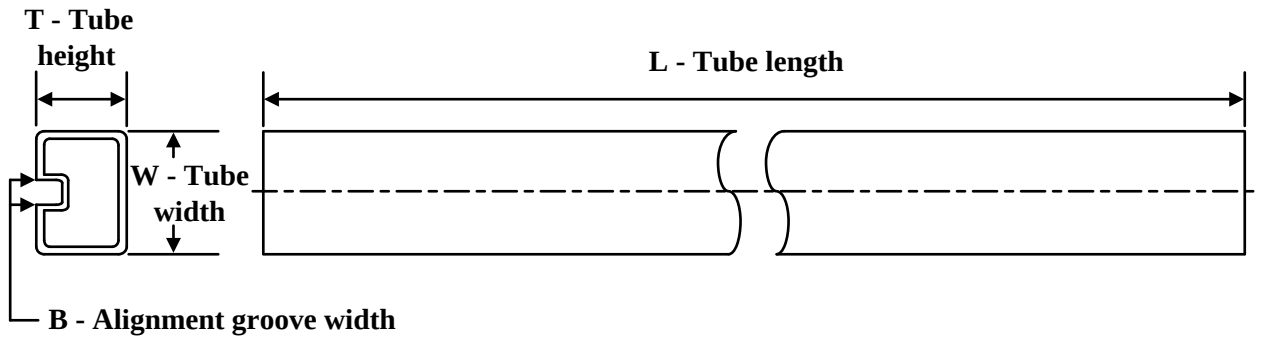
(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

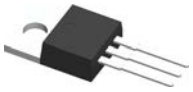
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CSD19506KCS	KCS	TO-220	3	50	534.5	33	7000	3.4
CSD19506KCS	KCS	TO-220	3	50	532	34.1	700	9.6
CSD19506KCS.B	KCS	TO-220	3	50	534.5	33	7000	3.4
CSD19506KCS.B	KCS	TO-220	3	50	532	34.1	700	9.6

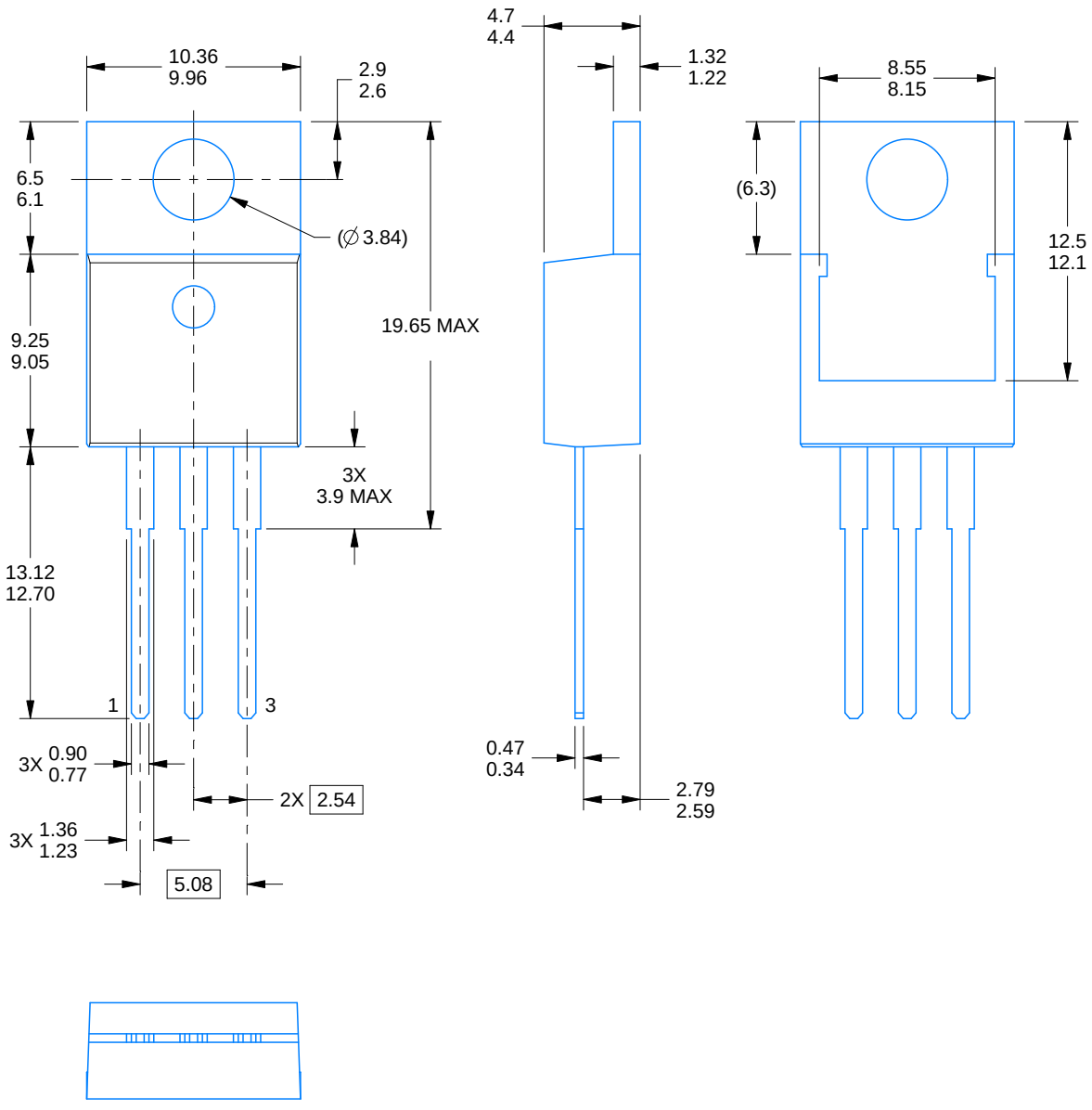
KCS0003B



PACKAGE OUTLINE

TO-220 - 19.65 mm max height

TO-220



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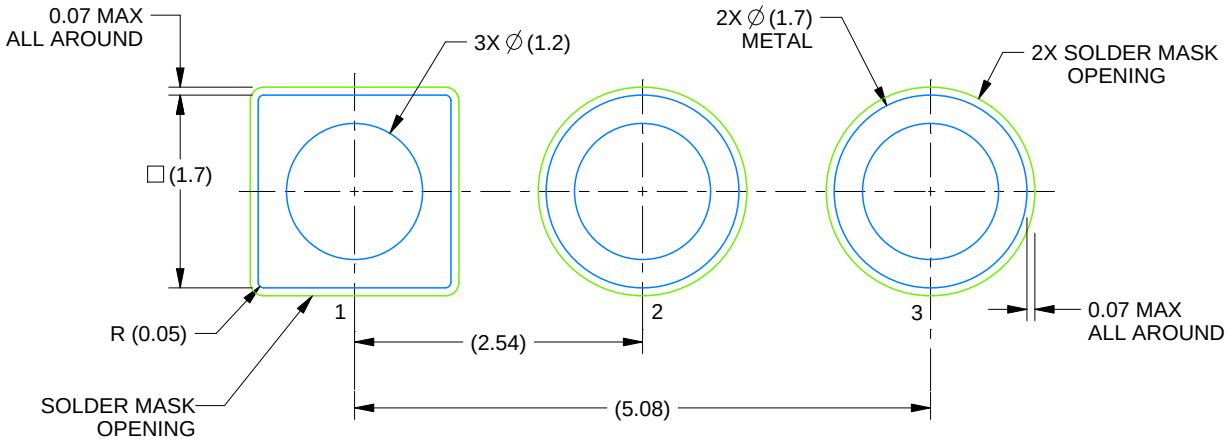
NOTES:

1. Dimensions are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC registration TO-220.



LAND PATTERN EXAMPLE
NON-SOLDER MASK DEFINED
SCALE:15X

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